no reaction will take place. On the other hand, if the temperature is too high, then the monosilicide phase of CoSi will be formed. Since the temperature window over which the metal-rich phase Co_2Si is formed is narrow, it is difficult to achieve only this phase during the first anneal. To extend the temperature window, a mixture of 80% Co and 20% Si may be deposited (e.g., by co-sputtering or evaporation from a $Si_{0.2}Co_{0.8}$ target). The temperature window for the formation of the Co_2Si out of the $Si_{0.2}Co_{0.8}$ mixture is about 337°C to about 487°C. The use of a 80% Si and 20% Co to extend the temperature window is described in U.S. Patent No. 6,323,130, to Cyril Cabral et. al, entitled "METHOD FOR SELF-ALIGNED FORMATION OF SILICIDE CONTACTS USING METAL SILICON ALLOYS FOR LIMITED SILICON CONSUMPTION AND FOR REDUCTION OF BRIDGING", filed on March 6, 2000, incorporated herein by reference.

Please replace the paragraph on page 18, line 3 with the following paragraph:

The silicon consumption may be further reduced if a mixture of Co and Si is deposited in the first step above. The process of using Co alloys was first disclosed in the above-mentioned U.S. Patent No. 6,323,130. Thus, instead of a pure Co deposition (step 1), Co is co-deposited with Si. The use of such a mixture of $Co_{1-x}Si_x$, is limited to about $x<0.3$, or otherwise bridging from source/drain to gate would occur. The reduction in the Si consumption from the wafer is achieved due to the following reasons: